AMENDMENTS TO THE CLAIMS

Claims 1-24 (canceled)

Claim 25 (original): A method for reading data from a programmable conductor random access memory cell, said method comprising:

activating an addressed word line containing said programmable conductor random access memory cell and transferring a logical value in said cell to an associated addressed bit line;

deactivating said addressed word line; and

sensing a logical value transferred to said bit line after said word line is deactivated.

Claim 26 (original): The method of claim 25, wherein said deactivating takes place a predetermined amount of time after said activating.

Claim 27 (original): The method of claim 25, wherein said sensing further comprises,

activating a first sense amplifier unit; and

activating a second sense amplifier unit a second predetermined time after said activating of said first sense amplifier unit.

Claim 28 (original): The method of claim 25, wherein said deactivating takes place a first predetermined amount of time after said activating of an addressed word line.

Claim 29 (original): The method of claim 28, wherein said first predetermined amount of time is after said activating of said first sense amplifier unit and before said activating of said second sense amplifier unit.

Claim 30 (original): The method of claim 28, wherein said first predetermined amount of time is before said activating of said first sense amplifier unit and before said activating of said second sense amplifier unit.

Claim 31 (original): A method for reading data from a programmable conductor random access memory cell, said method comprising:

activating an addressed word line containing said programmable conductor random access memory cell and transferring a logical value in said cell to an associated addressed bit line;

switching off an isolation transistor located on the associated addressed bit line and serially connecting a sense amplifier and said cell;

sensing a logical value transferred to said bit line after said word line is deactivated.

Claim 32 (original): The method of claim 31, wherein said switching off takes place a predetermined amount of time after said activating.

Claim 33 (original): The method of claim 31, wherein said sensing further comprises, activating a first sense amplifier unit; and

activating a second sense amplifier unit a second predetermined time after said activating of said first sense amplifier unit.

Claim 34 (original): The method of claim 32, wherein said switching off takes place a first predetermined amount of time after said activating of an addressed word line.

Claim 35 (original): The method of claim 34, wherein said first predetermined amount of time is after said activating of said first sense amplifier unit and before said activating of said second sense amplifier unit.

Claim 36 (original): The method of claim 34, wherein said first predetermined amount of time is before said activating of said first sense amplifier unit and before said activating of said second sense amplifier unit.

Claim 37 (original): A method for reading data from a programmable conductor random access memory cell, said method comprising:

pre-charging a first bit line coupled to the programmable conductor random access memory cell, said memory cell including a programmable conductor memory element;

pre-charging a second bit line;

increasing voltage on said first bit line;

switching on an access transistor of said cell to couple the programmable conductor memory element to said first bit line;

switching off the access transistor of said cell to decoupling the programmable conductor memory element from said first bit line;

sensing voltage on said first bit line and said second bit line to determine a logical state of said programmable conductor memory element;

wherein said switching off is performed before said sensing.

Claim 38 (original): A method for reading data from a programmable conductor random access memory cell, said method comprising:

switching on an isolation transistor to couple a first bit line to a sense amplifier, said first bit line also coupled to a programmable conductor memory element of the programmable conductor random access memory cell;

pre-charging said first bit line;

pre-charging a second bit line;

increasing voltage on said first bit line;

switching off said isolation transistor to decouple said programmable conductor memory element from said sense amplifier;

sensing voltage on said first bit line and said second bit line to determine a logical state of said programmable conductor memory element;

wherein said switching off is performed before said sensing.